TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7WZ245FU,TC7WZ245FK

Dual Bus Transceiver

Features

- High output drive : ±24 mA (min) at V_{CC} = 3 V
- Super high speed operation : t_{pd} = 5.0 ns(max)

at V_{CC} = 5 V, 50 pF

- Operation voltage range : V_{CC (opr)} = 1.65~5.5 V
- 5.5-V tolerant inputs

Marking

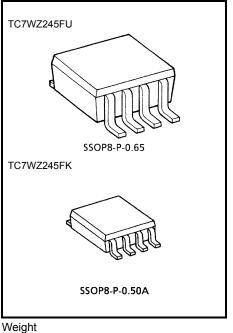
SM8

Z 245

- 5.5-V power down protection outputs
- Matches the performance of TC74LCX series when operated at 3.3-V V_{CC}
- Note : Do not apply a signal to any pins when it is the output mode. Damage may result. All floating (high impedance) bus pins must have their input levels fixed by means of pull-up or pull-down resistors.

US8

8888



WZ 245

SSOP8-P-0.65 : 0.02 g (typ.) SSOP8-P-0.50A : 0.01 g (typ.)

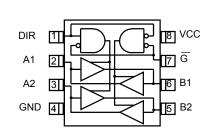
Maximum Ratings (Ta = 25°C)

Type name

Lot No.

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~6	V
DC input voltage	V _{IN}	-0.5~6	V
DC output voltage	V _{OUT}	-0.5~6	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	-20	mA
DC output current	IOUT	±50	mA
DC V _{CC} /ground current	ICC	±50	mA
Power dissipation	PD	300 (SM8) 200 (US8)	mW
Storage temperature	T _{stg}	-65~150	°C
Lead temperature (10 s)	ΤL	260	°C

Pin Assignment (top view)



Truth Table

INPUT		FUNC	OUTPUT		
G	DIR	A BUS	B BUS	001101	
L	L	OUTPUT	INPUT	A = B	
L	Н	INPUT	OTPUT	B = A	
Н	Х	High Im	Z		

X : Don't Care

Z : High Impedance

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Supply voltage		1.65~5.5	V	
	V _{CC}	1.5~5.5 (Note 1)	v	
Input voltage	VIN	0~5.5	V	
Output voltage	V _{OUT}	0~5.5 (Note 2)	V	
		0~ V _{CC} (Note 3)	v	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~20 (V_{CC} = 1.8 V \pm 0.15 V , 2.5 V \pm 0.2 V)	ns/V	
		0~10 (V_{CC} = 3.3 V \pm 0.3 V)		
		0~5 (V_{CC} = 5.5 V \pm 0.5 V)		

Note 1 : Data retention only

Note 2 : $V_{CC} = 0 V$

Note 3 : High or low state

Electrical Characteristics

Characteristics Symbol Test		ol Test Condition			٦	Ta = 25°C Ta = -40~85°C		0~85°C	Unit	
		Condition	V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit	
High-Level	VIH			1.65~1.95	V _{CC} × 0.75	_	_	V _{CC} × 0.75		- V
InputVoltage	VН	_		2.3~5.5	V _{CC} × 0.7	_	_	V _{CC} × 0.7		
Low-Level	VIL			1.65~1.95		—	$\begin{array}{c} V_{CC} \\ \times \ 0.25 \end{array}$	—	$\begin{array}{c} V_{CC} \\ \times \ 0.25 \end{array}$	
InputVoltage	VIL		_	2.3~5.5	_	—	V _{CC} × 0.3	_	$\begin{array}{c} V_{CC} \\ \times \ 0.3 \end{array}$	
				1.65	1.55	1.65		1.55	_	
			I _{OH} = -100 μA	2.3	2.2	2.3	—	2.2		
				3.0	2.9	3.0	—	2.9	_	
				4.5	4.4	4.5	—	4.4		
High-level output voltage	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -4 \text{ mA}$	1.65	1.29	1.52		1.29	_	
			$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.14		1.9		0.3 0.4 0.55
			$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.75	—	2.4	_	
			$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.62		2.3		
			$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.13		3.8	_	
		VIN = VIH or VIL	I _{OH} = 100 μA	1.65		0	0.1		0.1	
				2.3		0	0.1		0.1	
				3.0	_	0	0.1	_	0.1	
				4.5	_	0	0.1	_	0.1	
Low-level output voltage	V _{OL}		$I_{OH} = 4 \text{ mA}$	1.65		0.08	0.24		0.24	
			I _{OH} = 8 mA	2.3	_	0.1	0.3	_	0.3	
			I _{OH} = 16 mA	3.0		0.16	0.4	_	0.4	
			I _{OH} = 24 mA	3.0	_	0.24	0.55	_	0.55	
			I _{OH} = 32 mA	4.5		0.25	0.55		0.55	
Input leakage current	I _{IN}	$V_{IN} = 5.5 \text{ V or GND}$		0~5.5		—	±1	_	±10	μA
3-State Output Off-State Current	I _{OZ}	VIN=VIH or VIL VOUT=VCC or GND		1.65~ 5.5	_	_	±0.5	_	±5	μA
Power off leakage current	I _{OFF}	V_{IN} or $V_{OUT} = 5.5 V$		0.0	—	—	1	—	10	μA
Quiescent supply current	Icc	$V_{IN} = 5.5 \text{ V or GND}$		1.65~5.5	_	_	1		10	μA

AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Symbol Test Condition		Ta = 25°C Ta = -40~85°C			0~85°C	Unit	
Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
	t _{pLH}	$C_L = 15 \text{ pF}, R_L = 1 \text{ M}\Omega$	1.8 ± 0.15	2.0	—	15.0	2.0	16.5	ns
			2.5 ± 0.2	1.0		7.5	1.0	8.0	
Propagation delay time			3.3 ± 0.3	0.8		5.2	1.2	6.0	
Topagation delay time	t _{pHL}		5.0 ± 0.5	0.5	_	4.5	0.8	5.5	115
		$C_{1} = 50 \text{ pc}$ $P_{2} = 500 \text{ O}$	$\textbf{3.3}\pm\textbf{0.3}$	1.5	_	6.7	1.5	7.0	
		$C_L = 50 \text{ pF}, \text{ R}_L = 500 \Omega$	5.0 ± 0.5	0.8	_	5.0	0.8	5.3	
			1.8 ± 0.15	2.0	_	20.0	2.0	22.0	ns
3-state output Enable time	^t pZL pZH	$C_L = 50 \text{ pF}, \text{ R}_L = 500 \Omega$	2.5 ± 0.2	1.8	_	10.5	1.8	11.2	
			$\textbf{3.3}\pm\textbf{0.3}$	1.5	_	8.1	1.5	8.5	
			5.0 ± 0.5	0.8	_	5.5	0.8	5.8	
	t _{pLZ}	$C_L = 50 \text{ pF}, R_L = 500 \Omega$	1.8 ± 0.15	2.5		17.0	2.5	18.8	ns
3-state output Disable time			2.5 ± 0.2	1.5	—	8.6	1.5	9.1	
	t _{pLZ} t _{pHZ}		$\textbf{3.3}\pm\textbf{0.3}$	1.5		7.1	1.5	7.5	
			5.0 ± 0.5	0.3		4.7	0.3	5.0	
Output to output skew	tos _{LH}	(Note 4)	$\textbf{3.3}\pm\textbf{0.3}$			1.0		1.0	ns
	tos _{HL}	(NOLE 4)	5.0 ± 0.5			0.8		0.8	
Input capacitance	C _{IN}	DIR,DE	0		7		_	_	pF
Bus input capacitance	Cl / 0	An,Bn	5.5		8		_		pF
Power dissipation	C _{PD}	(Note 5)	3.3		29		_	—	рF
		. ,	5.5		33		—	_	Ч

Note 4 :Parameter guaranteed by desigh. $t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|$

Note 5 : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

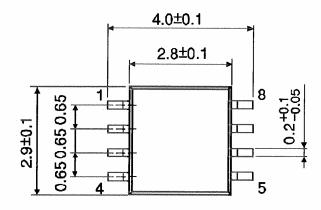
Average operating current can be obtained by the equation: $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$

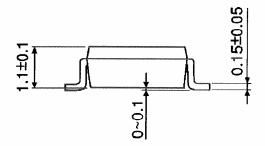
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Package Dimensions

SSOP8-P-0.65

Unit : mm

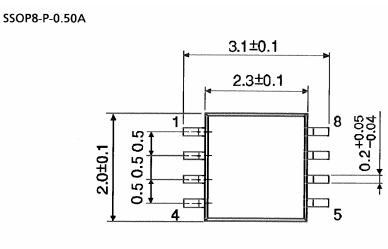


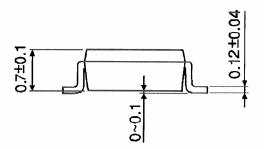


Weight: 0.02 g (typ.)

5

Package Dimensions





Weight: 0.01 g (typ.)

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Unit : mm

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